

# Real-time millikelvin thermometry in a spin qubit architecture

**Victor Champain**

V. Champain, V. Schmitt, B. Bertrand, H. Niebojewski, L. Hutin, R. Maurand, X. Jehl, C. Winkelmann, S. De Franceschi, B. Brun

Univ. Grenoble Alpes, CEA, Grenoble INP, IRIG-Pheliqs, Grenoble, France

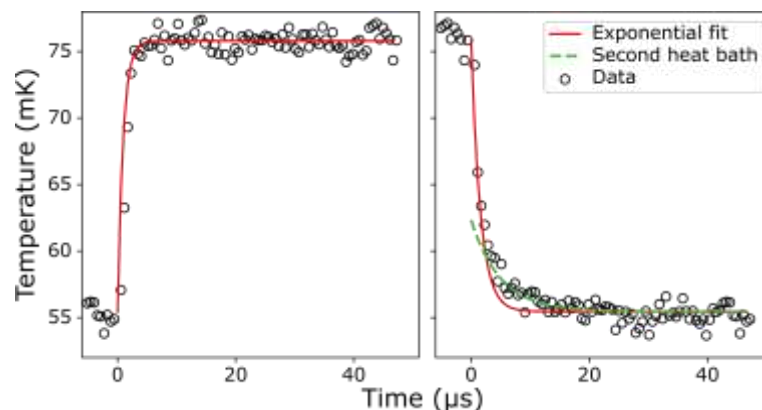
[Victor.champain@cea.fr](mailto:Victor.champain@cea.fr)

In the worldwide efforts to build the first useful quantum processor, semiconductor quantum dots[1] are attracting increasing interest owing to their scalability prospects[2]. In this approach, the qubits can be encoded in the spin degree of freedom of individual electronic charges localized in gate-defined potential wells. Recent works indicate that the heat generated by the manipulation and read-out of qubits constitutes a bottleneck for the efficient operation of large-scale quantum processors[3,4]. We present time-domain temperature measurements in the immediate environment of a semiconducting spin-qubit architecture. We take advantage of the temperature dependence of quantum capacitances in a silicon nanowire quantum dot array, which we read out via a radio-frequency tank circuit. Using two measurement configurations, we access the temperatures of both the local electron and phonon heat baths, respectively, with a noise equivalent temperature of  $3 \text{ mK}/\sqrt{\text{Hz}}$ , possible futures improvements of which are discussed. We illustrate (Fig.1) the time-domain capabilities of this thermometry technique by detecting the  $\mu\text{s}$ -scale temperature variations in response to short microwave bursts. This work represents a starting step towards the understanding and mitigating of the detrimental impact of dissipation on spin based quantum processors.

## References

- [1] D. Loss et al, Physical Review A, 57 (1998) 120.
- [2] L. Vandersypen et al, npj quantum Information, 3 (2017) 34
- [3] B. Undseth et al, Arxiv, 2304.12984 (2023)
- [4] W. Lawrie et al, Arxiv, 2109.07837 (2021)

## Figures



**Figure 1:** Real-time thermometry. Recording of the phonon temperature in a silicon nanowire, while (left panel) and after (right panel) irradiating a microwave burst as used for qubit manipulation.